

650V Super Junction Power MOSFET

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced trench gate super junction technology

Product Summary



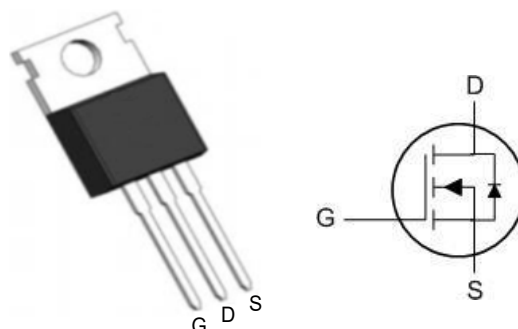
BVDSS	RDS(ON)	ID
650V	110 mΩ	24A

Description

The UD65R110T use super junction technology and design to provide excellent RDS(ON) with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

The UD65R110T meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO220AB Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	16	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	10	A
I_{DM}	Pulsed Drain Current ²	49	A
EAS	Single Pulse Avalanche Energy ³	300	mJ
I_{AS}	Avalanche Current	---	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	89	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	67	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.4	$^{\circ}C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	650	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	---	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=11A$	---	120	140	$m\Omega$
		$V_{GS}=4.5V$, $I_D=11A$	---	---	---	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	3.2	---	4.6	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=40V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	5	μA
		$V_{DS}=40V$, $V_{GS}=0V$, $T_J=100^\circ\text{C}$	---	220	---	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 30V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=20V$, $I_D=11A$	---	16.5	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	10	---	Ω
Q_g	Total Gate Charge	$V_{DS}=480V$, $V_{GS}=10V$, $I_D=11A$	---	46	---	nC
Q_{gs}	Gate-Source Charge		---	14	---	
Q_{gd}	Gate-Drain Charge		---	24	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{GS}=10V$, $V_{DS}=400V$, $R_G=27\Omega$, $I_D=11A$	---	60	---	ns
T_r	Rise Time		---	61	---	
$T_{d(off)}$	Turn-Off Delay Time		---	140	---	
T_f	Fall Time		---	31	---	
C_{iss}	Input Capacitance	$V_{DS}=100V$, $V_{GS}=0V$, $f=1MHz$	---	1595	---	pF
C_{oss}	Output Capacitance		---	90	---	
C_{rss}	Reverse Transfer Capacitance		---	1.6	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	16	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=11A$, $T_J=25^\circ\text{C}$	0.7	0.86	1.1	V
t_{rr}	Reverse Recovery Time	$I_F=11$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	120	---	nS
Q_{rr}	Reverse Recovery Charge		---	0.63	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3.The EAS data shows Max. rating . The test condition is $T_J=25^\circ\text{C}$, $V_{DD}=200V$, $V_{GS}=10V$, $L=50mH$

4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power

dissipation.

Typical Performance Characteristics

Fig 1. Output Characteristics ($T_j=25^\circ\text{C}$)

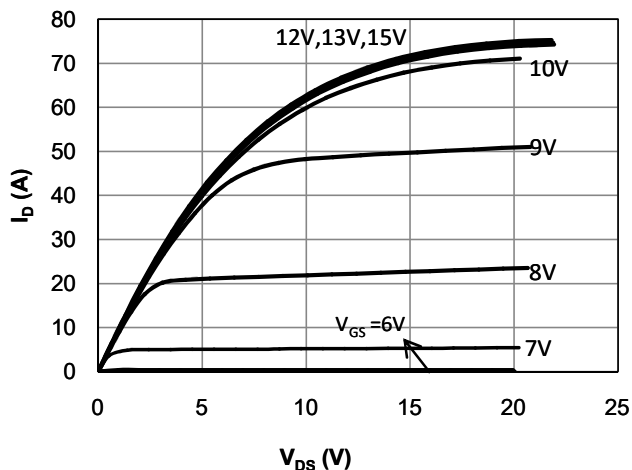


Fig 2. Output Characteristics ($T_j=150^\circ\text{C}$)

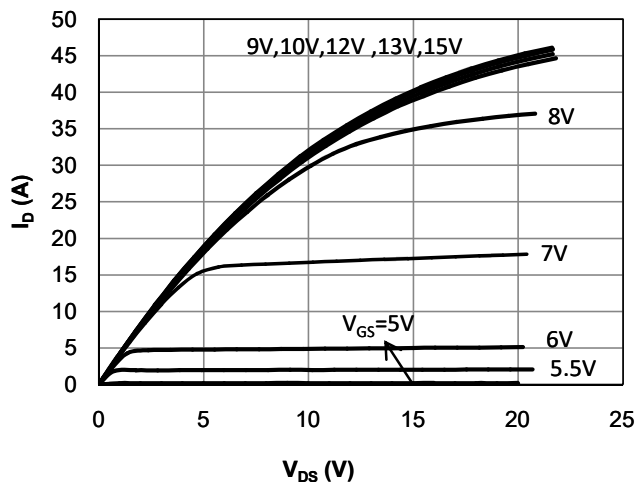


Fig 3: Transfer Characteristics

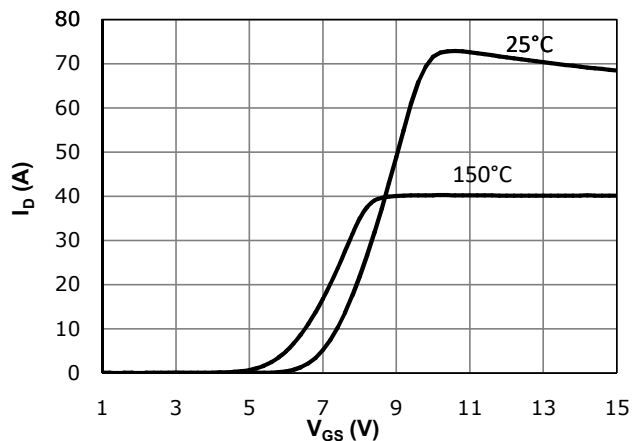


Fig 4: V_{TH} vs. T_j Temperature Characteristics

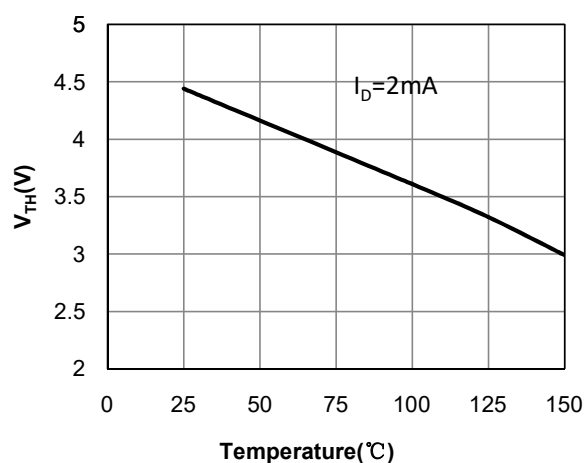


Fig 5: $R_{DS(on)}$ vs. I_{DS} Characteristics ($T_j=25^\circ\text{C}$)

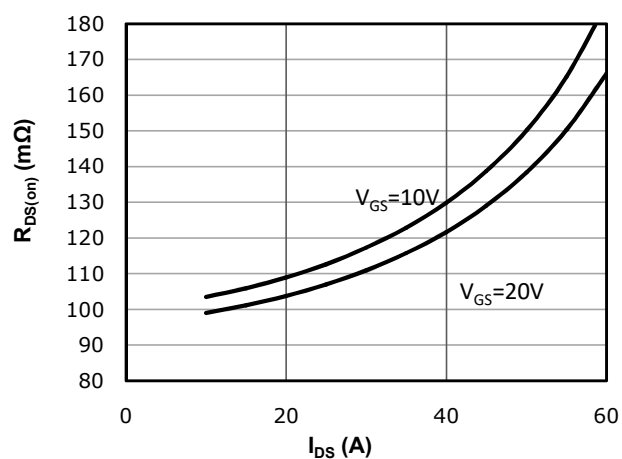
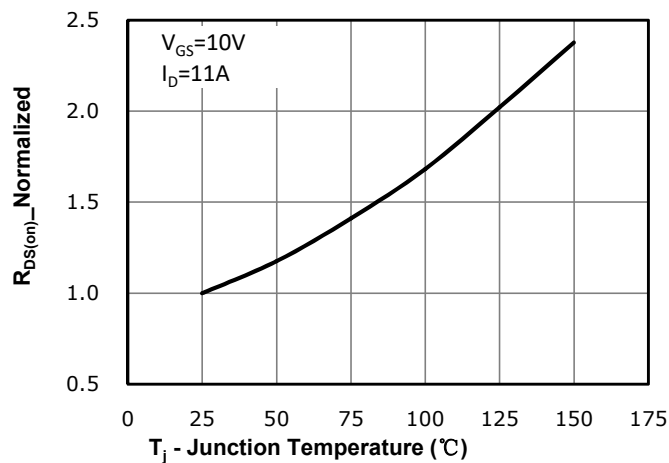


Fig 6: $R_{DS(on)}$ vs. Temperature



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Fig 7: BV_{DSS} vs. Temperature

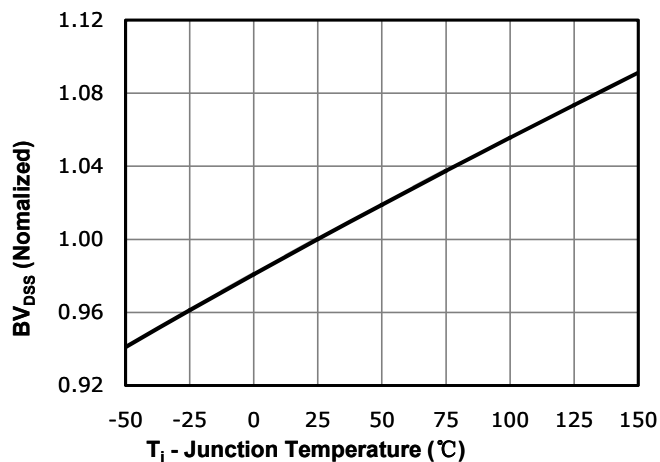


Fig 8: $R_{DS(on)}$ vs. Gate Voltage

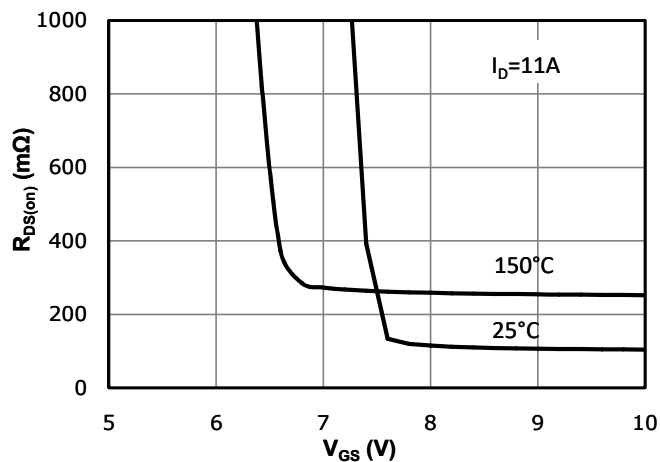


Fig 9: Body-diode Forward Characteristics

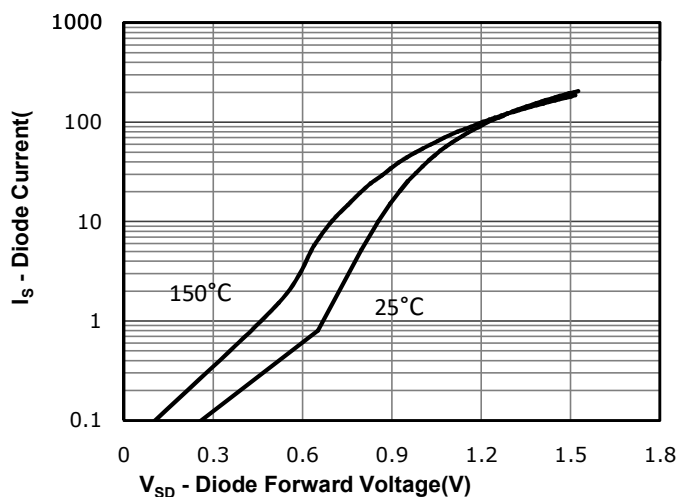


Fig 10: Gate Charge Characteristics

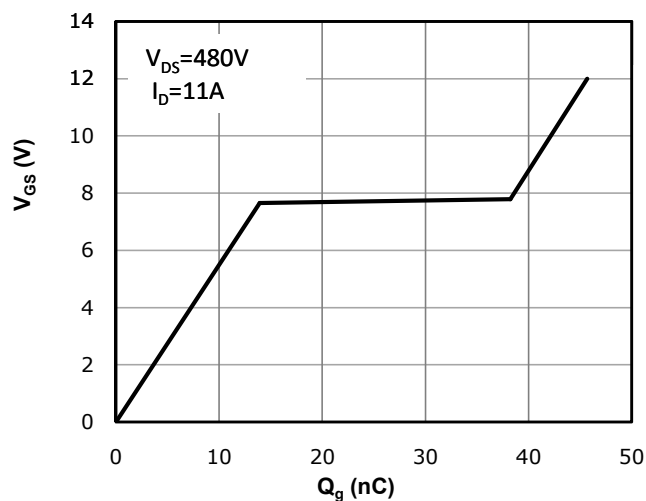


Fig 11: Capacitance Characteristics

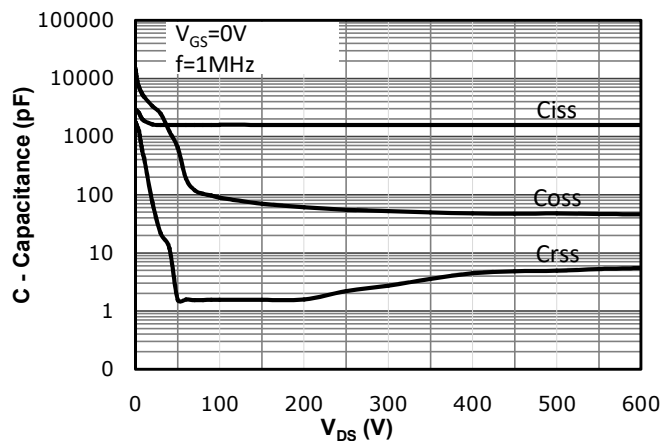


Fig 12: Safe Operating Area

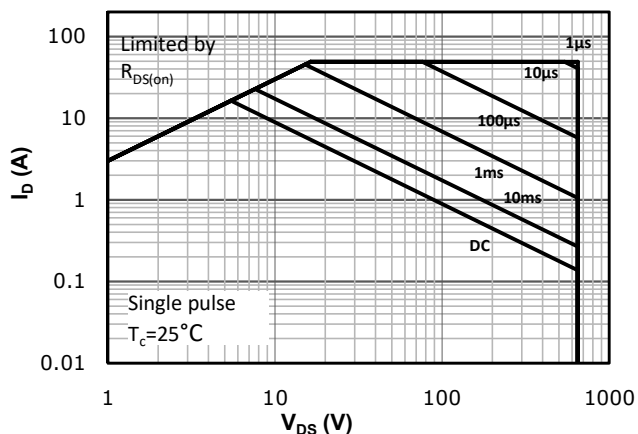
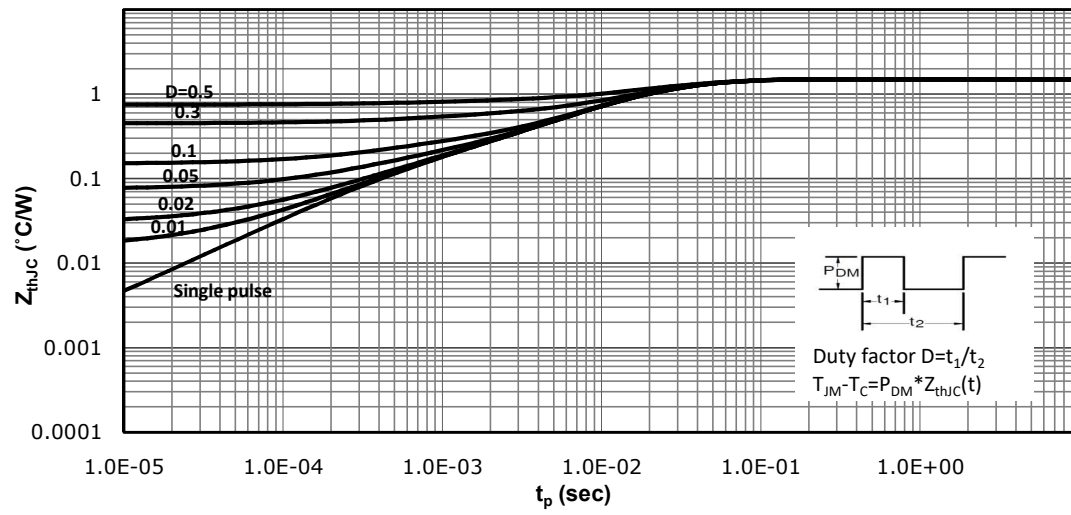
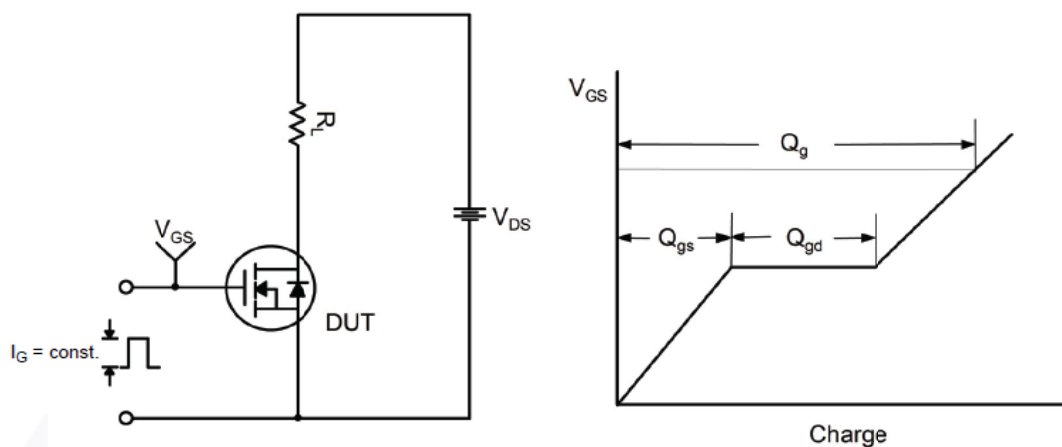




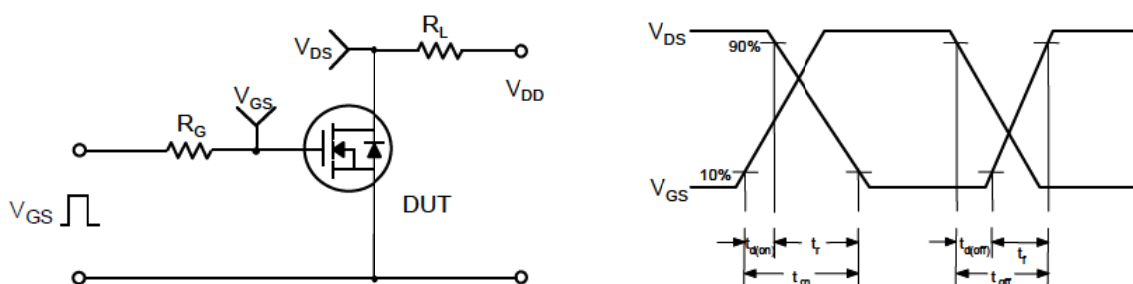
Fig 13: Max. Transient Thermal Impedance



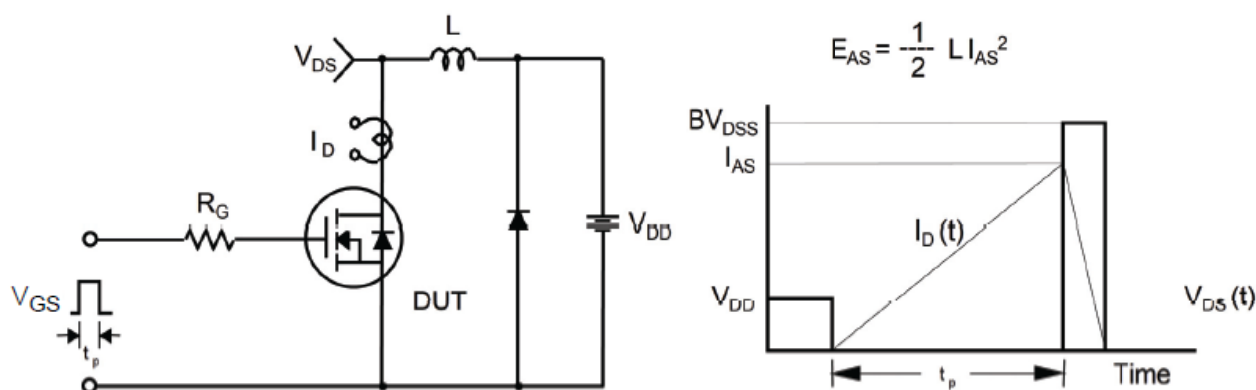
Gate Charge Test Circuit & Waveform



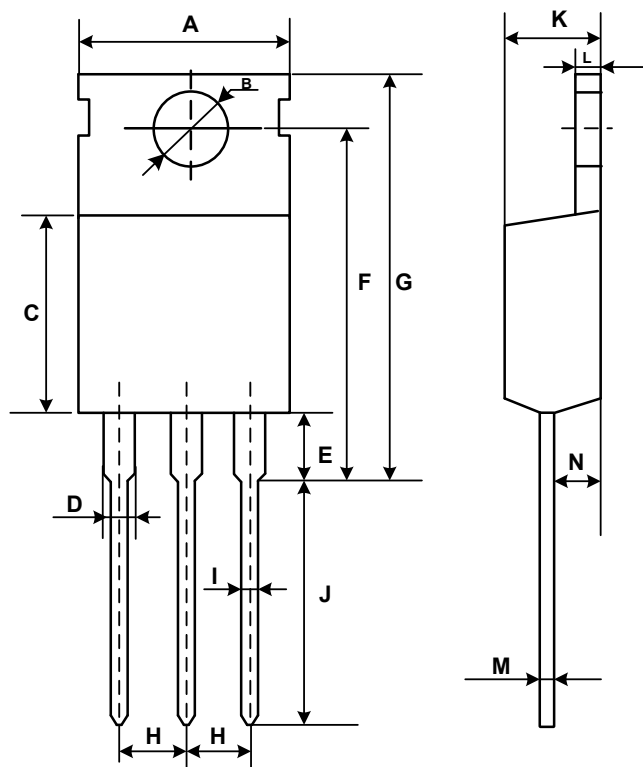
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions for TO-220AB



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.70	10.30
B	3.40	3.80
C	8.80	9.40
D	1.17	1.47
E	2.60	3.50
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60